

# Low-Temperature Solution-Processed Thin SnO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub> Double Electron Transport Layers Towards 20% Efficient Perovskite Solar Cells

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**Abstract**— We present planar perovskite solar cells (PSCs) incorporating thin SnO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub> double electron transport layers between the perovskite and an indium tin oxide (ITO) bottom electrode. When measured under 1 sun illumination, we obtained a maximum power conversion efficiency (PCE) of 20.1% and a steady state efficiency of 17.8% for the best cell. These values were ~ 20-30% higher in relative terms than that of cells with SnO<sub>2</sub> only (i.e. a maximum PCE of 15.3% and a steady state PCE of 14.9%). Insertion of the thin UV-irradiated solution-processed nanoparticle Al<sub>2</sub>O<sub>3</sub> interlayer effectively enhanced the wettability of the electron transport layer, provided enhanced interface area, as well as a lower work function, leading to improved charge extraction. Incorporation of an Al<sub>2</sub>O<sub>3</sub> layer between the perovskite and SnO<sub>2</sub> layers also improved the rectification ratios of the diodes as well as both series and shunt resistances. Our devices are fabricated using fully solution-processed transport and active semiconducting layers processed at low temperatures ( $\leq 150$  °C).

**Index Terms**— electron transport layer, maximum power point tracking, SnO<sub>2</sub> layer, SnO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub> double layer, planar perovskite solar cell.

## I. INTRODUCTION

Organic-inorganic hybrid perovskite solar cells (PSCs) have attracted tremendous attention due to their high power conversion efficiency (PCE), and low-cost fabrication processes [1-7]. The highest efficiency of the PSCs reported so far is 24.2% [8]. In order to achieve high efficiencies, great care has been put into material processing, device processing, architectures and interfaces [9, 10]. Generally, PSCs are composed of p-i-n or n-i-p configurations where the photo-absorbing perovskite layer is incorporated between a hole

transport layer (HTL) and an electron transport layer (ETL). These transport layers extract photo-generated electrons and holes from the perovskite towards the electrodes. To date, several electron transport layers (ETLs) have been developed in the popular n-i-p configuration, including SnO<sub>2</sub> [10, 11], ZnO [12-14], TiO<sub>2</sub>, [15]. “Notably, fullerenes have also been used as effective ETLs in both n-i-p and p-i-n perovskite solar cells configurations due to a number of capabilities including passivating surface defects and filtering the UV light reaching the photoabsorbing layer. Fullerene-based ETLs not only improve the performance of the PSCs but also reduce the hysteresis during the JV scans in forwards and reverse directions [16, 17]. TiO<sub>2</sub> has historically been the most common ETL used in n-i-p PSCs which is typically annealed at high temperature (>450 °C), in a process that is flexible and also adaptable to 3D nanostructuring via a variety of approaches, including nanosphere templating to aid photon recycling [18]. Here, we used a SnO<sub>2</sub> ETL due to its potential properties including high optical transparency, and the wider band gap compared to TiO<sub>2</sub> ETL [19-21]. The SnO<sub>2</sub> ETL is processed at low temperature ( $\leq 150$  °C) along with UV light treatment. However, the performance of PSCs utilizing “low-temperature” SnO<sub>2</sub> deposited from SnCl<sub>2</sub>·2H<sub>2</sub>O precursor solution dissolved in hydrous ethanol (0.1M concentration) is not always at the same level as that obtained from “high-temperature alternatives”, and show less reproducibility and significant hysteresis due to the presence of surface traps at the interface of SnO<sub>2</sub> and perovskite layer. Several treatments to the SnO<sub>2</sub> layer including UV light exposure [11], water vapor treatments [22], together with plasma-enhanced atomic-layer deposition (PEALD) [23] have been carried out in order to enhance the performance of SnO<sub>2</sub> based PSCs. Another route consists in developing composite ETLs.

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Recently, we have shown that applying a thin MgO (magnesium oxide) coating over the SnO<sub>2</sub> delivered a ~ 20% increase in PCE compared to devices with SnO<sub>2</sub> only ETLs [4]. Here, we introduce a different oxide nanolayer, made of Al<sub>2</sub>O<sub>3</sub> nanoparticles (NPs) with average size of <50 nm, rather than the customary thicker mesoporous TiO<sub>2</sub> or Al<sub>2</sub>O<sub>3</sub> scaffolds typically used in PSCs [24-26], over the SnO<sub>2</sub> reaching an enhancement of 20-30% in PCE compared to cells with SnO<sub>2</sub> only, utilizing exclusively low-temperature fabrication procedures (i.e. below 150 °C) and the most simple of perovskite active layers, i.e. CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub>.

## II. EXPERIMENTAL

### A. Materials

Al<sub>2</sub>O<sub>3</sub> (Aluminum oxide) nanopowder, <50 nm particle size, Tin chloride (SnCl<sub>2</sub>·2H<sub>2</sub>O) dehydrate, 4-tert-butylpyridine (TBP), Li-bis(trifluoromethanesulfonyl) imide (Li-TFSI) and solvents DMSO (Dimethyl sulfoxide anhydrous, ≥99.9%), DMF (*N,N*-Dimethylformamide anhydrous, 99.8%), ethanol (99.8%), diethyl ether (99.0%) were purchased from Sigma-Aldrich. Lead(II) Iodide (99.99%, trace metals basis) was purchased from TCI Deutschland gmbh. Methylammonium iodide (CH<sub>3</sub>NH<sub>3</sub>I) and FK209 cobalt salt (98%) were purchased from Dyesol Limited. 2,2',7,7'-tetrakis-(*N,N*-di-*p*-methoxyphenylamine)-9,9'-spirobifluorene (spiro-meotad) (≥99.8%) was purchased from Borum New Material technology Ltd.

### B. Device Fabrication

Glass/ITO substrates (Kintec -8Ω/□, 25x25 mm) were realized over specific layout of the ITO electrode using a raster scanning laser (Nd:YVO<sub>4</sub>, λ = 1064 nm, 8 ns, pulsed at 10 kHz with a fluence of 260 mJ/cm<sup>2</sup>) [27]. The patterned ITO substrates were cleaned in ultrasonic bath using acetone, and isopropanol for 15 minutes each, followed by drying with compressed air. The substrates were transferred under a UV-lamp with an estimated power density of 225 mW cm<sup>-2</sup> (Dymax EC 5000 UV lamp with a metal-halide bulb PN38560 Dymax that contains no UV-C) for 10 minutes. The UV-light treatment over glass/ITO surface assist the removal of organic residues and lead to enhance the wettability of ITO cathode. For the fabrication of ITO/SnO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub>/CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub>/Spiro-MeOTAD/Au perovskite solar cell devices, SnO<sub>2</sub> solution, 0.1M in ethanol from SnCl<sub>2</sub>·2H<sub>2</sub>O precursor bought from sigma Aldrich [28] was spin coated over Glass/ITO substrates at 1500 rpm for 30 second and followed by 2500 rpm for next 30 second for obtaining a thickness of 24-30 nm, which was confirmed by profilometer. The substrates were annealed on a hotplate at 150 °C in ambient air for 1 hour, followed by a UV-light irradiation treatment for 15 minutes.

The Al<sub>2</sub>O<sub>3</sub> solution was prepared by diluting Al<sub>2</sub>O<sub>3</sub> dispersion (Al<sub>2</sub>O<sub>3</sub> nanoparticles, <50 nm particle size (DLS), 20 wt. % in isopropanol) in isopropanol (1.78 mg/ml) followed by

overnight stirring at room temperature. The Al<sub>2</sub>O<sub>3</sub> layer was spin coated over the SnO<sub>2</sub> layer at 1000, 3000, 5000 and 6000 rpms for 30 seconds for each concentration. The substrates with Al<sub>2</sub>O<sub>3</sub> layer were annealed at 150 °C for 1 hour in air and further subjected to a UV light irradiation treatment for 15 minutes. The perovskite films were deposited by the so-called single-step solvent-engineering method[29]. The perovskite solution was prepared by dissolving mixture of 1.41 M of PbI<sub>2</sub> and 1.41 M CH<sub>3</sub>NH<sub>3</sub>I in DMF: DMSO 9:1 (v/v) solvents and overnight stirring at room temperature.

The perovskite solution was deposited over ETLs layer via spin coating at spin speeds of 1000 rpms for 10 seconds and then 5000 rpms for 45 sec. Next, 0.7 mL of diethyl ether were dropped on the rotating substrates when 35 seconds are remaining. Further to obtain a homogeneous and mirror-like black perovskite film these were successively subjected to a two-step annealing process, carried out at 50 °C for 2 minutes and then at 100 °C for 10 minutes [4, 28, 30, 31].

As a hole transport layer, Spiro-OMeTAD solution in chlorobenzene (74 mg·mL<sup>-1</sup>) was deposited via spin coating at spin speed of 2000 rpm for 20 under inert atmosphere. The solution was doped with LiTFSI (16.6μL/mL), TBP (26.77μL/mL), and cobalt(III) complex (7.2 μL/mL) and kept overnight at room temperature in inert atmosphere [30]. Finally, the samples were inserted in to high vacuum chamber (10<sup>-6</sup> mbar) to evaporate gold (Au) as back contacts (thickness~80nm) through a shadow mask.

### C. Device measurements

The perovskite solar cells were tested under a AM1.5G Class A ABET solar simulator at an intensity of 1000 W/m<sup>2</sup> (1 sun) illumination conditions, calibrated with a EKO MS-602 pyranometer. Current-voltage characteristics were obtained using a digital source meter (Keithley 2420) [37]. The LabVIEW parameters including voltage step and delay time for data point scans were fixed at 30 mV and 200 ms respectively during the measurements. Solar cells were measured with an aperture of 0.1 cm<sup>2</sup> using a black tape mask and fixed in a Teflon holder to keep them flat under sun light illumination. The average PV parameters, shown in the main text were measured in reverse scan. Forward scans are also reported for the best cells as well as the steady state power conversion efficiency [4, 26, 32].

The EQE (external quantum efficiency) measurements of perovskite solar cells were carried out using a homemade apparatus consisting of an amperometer (Keithley 2612) and a monochromator (Newport 74000).

The dark J-V characteristics and open circuit voltage rise/decay measurements were carried out using a modular testing platform (Arkeo - Cicci research s.r.l.). The Arkeo system refers to a white LED array (4200 K) which can be tuned up to 200 mW/cm<sup>2</sup> of optical power intensity and high speed source meter unit [33] [39].

**Table 1.** Averages of the PV parameters and the maximum PCE of  $\text{CH}_3\text{NH}_3\text{PbI}_3$  planar perovskite solar cells based on  $\text{SnO}_2$  and  $\text{Al}_2\text{O}_3$  spun over the  $\text{SnO}_2$  surface from the 1.78mg/ml solution at different spin speeds.

$\text{Al}_2\text{O}_3$ conc.(mg/ml)	Electron Transport Layer	$\text{Al}_2\text{O}_3$ Spin Speed (rpm)	$J_{sc}$ [ $\text{mA}/\text{cm}^2$ ]	$V_{oc}$ [V]	FF [%]	PCE [%]	PCE Max[%]
None	$\text{SnO}_2$	No	$20.08 \pm 0.68$	$1.08 \pm 0.02$	$66.80 \pm 1.43$	$14.58 \pm 1.07$	15.3
1.78	$\text{SnO}_2/\text{Al}_2\text{O}_3$	1000	$21.53 \pm 0.60$	$1.13 \pm 0.005$	$72.34 \pm 2.00$	$17.61 \pm 0.66$	18.6
	$\text{SnO}_2/\text{Al}_2\text{O}_3$	3000	$22.87 \pm 1.22$	$1.14 \pm 0.011$	$73.14 \pm 1.96$	$19.10 \pm 0.97$	20.1
	$\text{SnO}_2/\text{Al}_2\text{O}_3$	5000	$20.92 \pm 0.41$	$1.12 \pm 0.004$	$75.15 \pm 1.83$	$17.73 \pm 0.84$	18.4
	$\text{SnO}_2/\text{Al}_2\text{O}_3$	6000	$20.75 \pm 0.68$	$1.12 \pm 0.005$	$72.77 \pm 2.02$	$16.94 \pm 0.12$	17.1

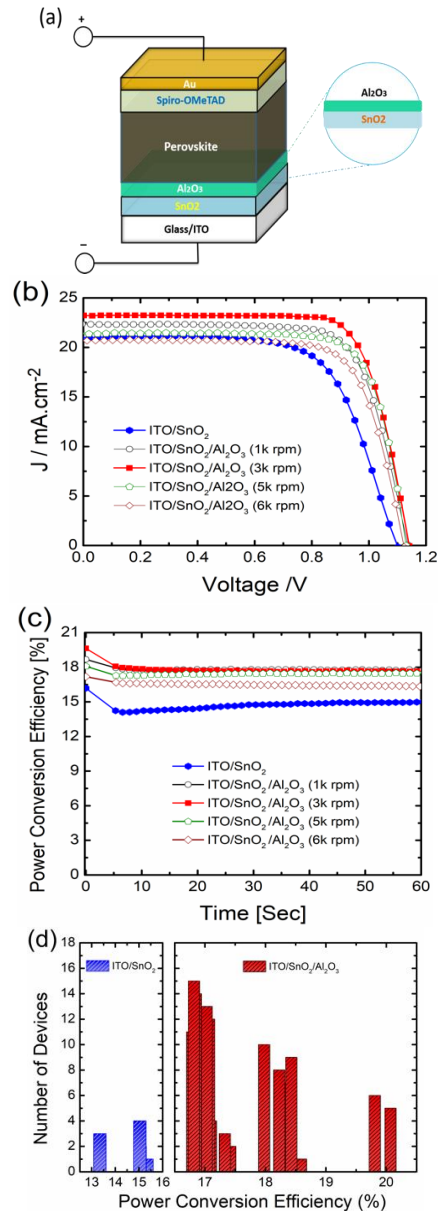
#### D. Characterization

AFM measurements were obtained with peak force tapping imaging technique, employing a Bruker Dimension Icon microscope.

### III. RESULTS AND DISCUSSION

The device architecture of the PSCs we fabricated, i.e. ITO/ $\text{SnO}_2$ / $\text{Al}_2\text{O}_3$ / $\text{CH}_3\text{NH}_3\text{PbI}_3$ /Spiro-MeOTAD/Au is shown in figure 1 (a). It consisted of a compact  $\text{SnO}_2$  electron transport layer, known to deliver favorable electron extraction properties, deposited over glass/ITO substrates via low temperature solution processing [28, 34], a  $\text{CH}_3\text{NH}_3\text{PbI}_3$  perovskite semiconductor spin-coated via single-step solvent engineering technique[29], a Spiro-OMeTAD (2,2',7,7'-tetrakis-(N,N-di-p-methoxyphenylamine)-9,9'-spirobifluorene) as hole transport layer, and evaporated Au as top electrode [26]. In particular, we introduced thin  $\text{Al}_2\text{O}_3$  nanoparticle interlayers of different thickness between the  $\text{SnO}_2$  and the perovskite layers by preparing commercially available  $\text{Al}_2\text{O}_3$  nanoparticle solution diluted in isopropanol. Three different concentrations (0.59, 0.99 and 1.78mg/ml) of  $\text{Al}_2\text{O}_3$  NPs were optimized and 1.78mg/ml was found the best. The  $\text{Al}_2\text{O}_3$  solutions were deposited over the  $\text{SnO}_2$  ETL at different spin speeds (1, 3, 5 and 6 thousand revolutions per minute, or k rpm) in order to investigate which processing parameters were optimal for device performance [35].

Here we focus only on the formulation that delivered the best-performing solar cells, i.e. those from the 1.78mg/ml  $\text{Al}_2\text{O}_3$  solution. The current density-voltage (J-V) characteristics of the best performing PSCs with  $\text{Al}_2\text{O}_3$  interlayers deposited at different spin speeds measured under 1 sun illumination are shown in figure 1 (b) along with cells with  $\text{SnO}_2$  only ETL. The average photovoltaic (PV) parameters of the cells at 1 sun: short circuit current ( $J_{sc}$ ), open circuit voltage ( $V_{oc}$ ), fill factor (FF) and power conversion efficiency (PCE) are reported in Table 1. We carried out these tests on 12 different cells for each type obtaining consistent results.



**Fig. 1.** (a) Device structure of the ITO/ $\text{SnO}_2$ / $\text{Al}_2\text{O}_3$ / $\text{CH}_3\text{NH}_3\text{PbI}_3$ /Spiro-MeOTAD/Au perovskite solar cell where  $\text{Al}_2\text{O}_3$  (1.78mg/ml) NPs concentration in isopropanol, (b) J-V curves of best performing perovskite solar cell devices based on ITO/ $\text{SnO}_2$  and ITO/ $\text{SnO}_2$ / $\text{Al}_2\text{O}_3$  bilayers where the  $\text{Al}_2\text{O}_3$  was spin coated at different speeds, including 1k rpm, 3k rpm, 5k rpm and 6k rpm under AM1.5G, 1000  $\text{W}/\text{m}^2$  irradiation, (c) The evolution of the stabilized power conversion efficiency of the best perovskite solar cells over time measured at constant bias near the maximum power point under AM1.5G, 1000  $\text{W}/\text{m}^2$  irradiation. (d) Statistics of PCE distribution for perovskite devices with  $\text{SnO}_2$  and  $\text{SnO}_2/\text{Al}_2\text{O}_3$  (12 devices).

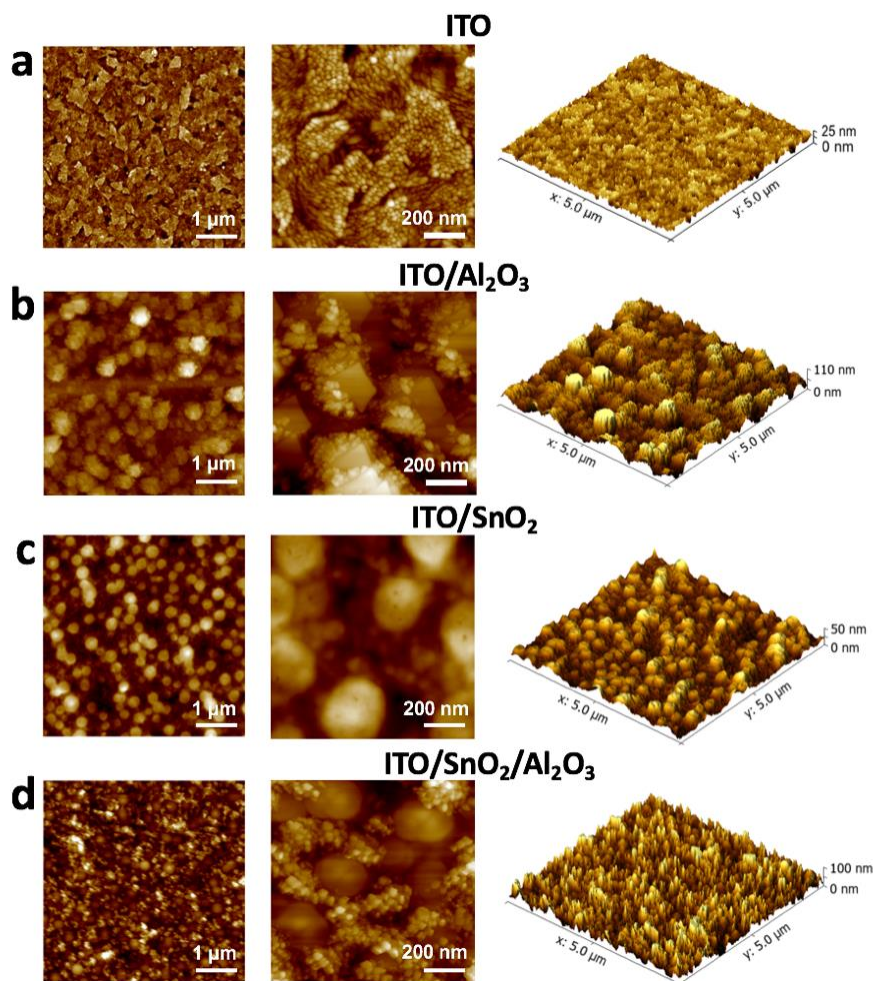
The PSCs with only SnO<sub>2</sub> ETL result in an average PCE of 14.6% (and a maximum PCE of 15.3%) along with a J<sub>SC</sub> of 20.1 mA/cm<sup>2</sup>, V<sub>OC</sub> of 1.08 V and FF of 66.8%. The PV performance of PSCs was significantly enhanced after introducing the Al<sub>2</sub>O<sub>3</sub> interlayer between the SnO<sub>2</sub> and the perovskite films, particularly so at the most favourable concentration (1.78mg/ml) and spin speed (3k rpm). The PCE was measured to be 30% higher in relative terms compared to the SnO<sub>2</sub> only counterparts resulting in an average PCE value of 19.1% and a maximum PCE of 20.1% for the best cell.

This increment in PCE is a result of an enhancement in all PV parameters brought about by the incorporation of Al<sub>2</sub>O<sub>3</sub>. The EQE (external quantum efficiency) was recorded for the best performing device. The integrated J<sub>sc</sub> calculated from the EQE with the AM1.5G spectrum was within <10% in relative terms compared to the J<sub>sc</sub> measured under 1 sun illumination for cells both with and without Al<sub>2</sub>O<sub>3</sub> layer which is well within that expected under these comparisons[36-38].

75.7 %, V<sub>oc</sub> = 1.14V and PCE = 20.1% in reverse scan (and J<sub>sc</sub> = 23.4 mA/cm<sup>2</sup>, FF = 71.6%, V<sub>oc</sub> = 1.10V and PCE = 18.5% in forward scan). The corresponding values for the best cells with ITO/SnO<sub>2</sub> only electrodes were J<sub>sc</sub> = 20.5 mA/cm<sup>2</sup>, FF = 68%, V<sub>oc</sub> = 1.10V and PCE = 15.3% in reverse scan (and J<sub>sc</sub> = 20.6 mA/cm<sup>2</sup>, FF = 63%, V<sub>oc</sub> = 1.08V and PCE = 14.0% in forward scan). Notably, the steady-state efficiencies for all the best devices with different ETLs are reported in Figure 1c versus time (i.e. for 60 seconds) under 1 sun illumination. Measured after 60s, the steady state PCE for the SnO<sub>2</sub>-only cell was 14.9% (measured at 0.721V) whereas it increased to 17.8% when adding Al<sub>2</sub>O<sub>3</sub> deposited at 3 k rpm (at 0.767 V).

The steady state measurements of figure 1c show that the cells have good measurement stability. The statistics of PCE distribution for perovskite devices with SnO<sub>2</sub> and SnO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub> was reported in figure 1 (d).

Tapping-mode atomic force microscopy (AFM)



**Figure 2.** Atomic Force Microscopy (AFM) images of (a) ITO, (b) ITO/Al<sub>2</sub>O<sub>3</sub>, (c) ITO/SnO<sub>2</sub> and (d) ITO/SnO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub> surface. The scale bar in the first column is 1 μm. The scale bar in the second column is 200nm. The third column shows the 3D images on a 5 μm x 5 μm area where roughness can be gauged.

The photovoltaic parameters for the best cell with the ITO/SnO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub> electrode were J<sub>sc</sub> = 23.2 mA/cm<sup>2</sup>, FF =

measurements of ITO-only, ITO/Al<sub>2</sub>O<sub>3</sub>, ITO/SnO<sub>2</sub> and ITO/SnO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub> layers were performed to investigate the

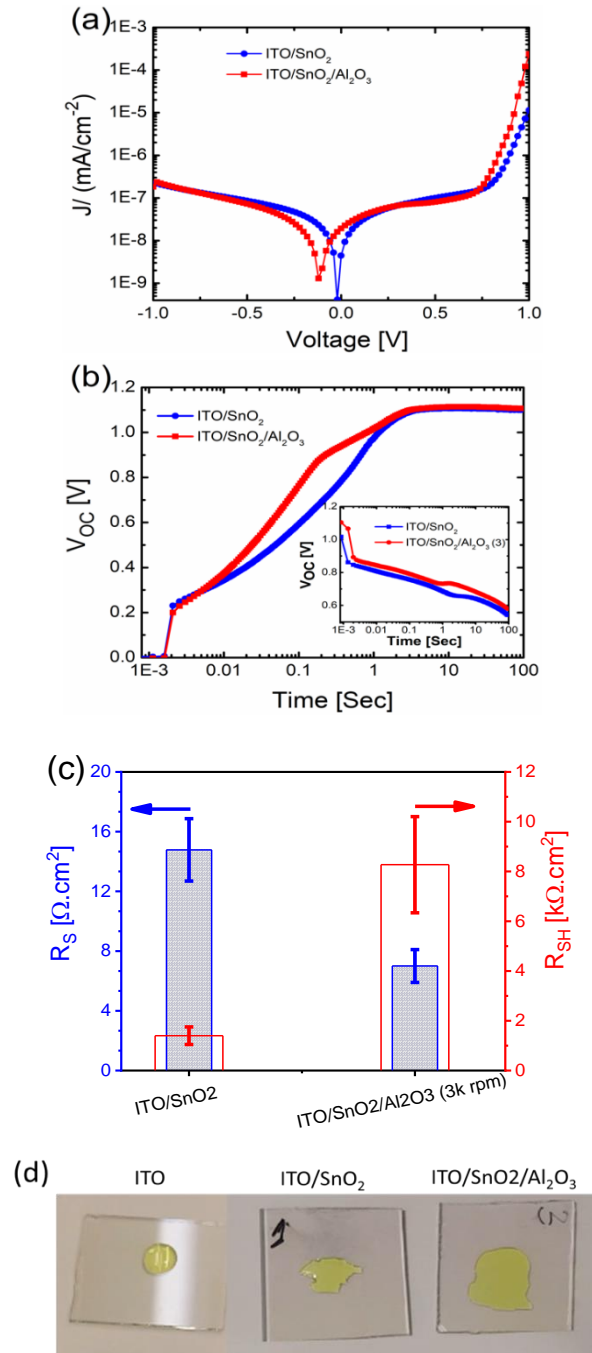


surface morphology and roughness. Figure 2 (a) shows the surface morphology of the ITO films which were very flat (2.8 nm rms). Addition of the Al<sub>2</sub>O<sub>3</sub> on ITO increased the roughness to 25nm and produced a mixed structure of smaller nanoparticles of 15-30nm average dimension and bigger crystallites of the order of 200nm (figure 2b). Differently, the surface roughness of the ITO/SnO<sub>2</sub> was small, i.e. ~9 nm, and showed the presence of round/cylindrical formations of 150-300nm diameter (figure 2c). The smaller sized particles, which can be noted well below the bigger domes, may well be ITO if not smaller sized SnO<sub>2</sub>. Finally, the ITO/SnO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub> layer in Figure 2d, with a 22nm roughness (higher than SnO<sub>2</sub> only), resembles in fact the combination of the SnO<sub>2</sub> and the Al<sub>2</sub>O<sub>3</sub> films, with larger crystallite/agglomerates (150-200nm) and the smaller nanoparticles. The latter, due to the good visual match with those 15-30nm diameter nanoparticles present in figure 2b can be attributed to Al<sub>2</sub>O<sub>3</sub> and may provide a possible explanation of the capability of the Al<sub>2</sub>O<sub>3</sub> in reducing defects and filling pinholes in the composite ETL. The higher roughness of the composite SnO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub> layer (22nm rms) compared to the SnO<sub>2</sub>-only layer (9nm rms) will also determine a different interface when growing the perovskite film as well as a larger electronic interface area.

The dark IV characteristics of best performing PSCs with and without Al<sub>2</sub>O<sub>3</sub> interlayer are shown in figure 3 (a). The PSCs with SnO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub> double layer delivered a rectification ratio (calculated at +1 V/-1 V) of  $1.31 \times 10^3$  which was significantly higher compared to that of the cell with only SnO<sub>2</sub> layer ( $1.89 \times 10^2$ ), showing the higher rectification behavior which is mainly due to a higher forward bias current at 1V. We noticed an increase in fill factor (from 66.1% to 73.1%) for SnO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub> measured under 1 sun illumination. In fact, Al<sub>2</sub>O<sub>3</sub> over SnO<sub>2</sub> layer provided a better contact resistance between the perovskite and ETL layers [39, 40] as shown in figure 3c.

Al<sub>2</sub>O<sub>3</sub> over SnO<sub>2</sub> enhanced the charge transport and electron extraction properties of the PSCs[41]. The OCVR measurements (open circuit voltage rise) under illumination (see figure 3(b)) show that the SnO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub> devices delivered a faster rise in Voc compared to the cells with SnO<sub>2</sub> only. This is due to better charge transport from perovskite layer to the charge transport layer and faster extraction. The thin Al<sub>2</sub>O<sub>3</sub> layer reduces charge recombination at the interface between perovskite and bottom electrode, leading to enhanced performance. In particular, the series resistance (R<sub>s</sub>) and shunt resistance (R<sub>sh</sub>) of the cells were calculated for both with and without Al<sub>2</sub>O<sub>3</sub> (see figure 3(c)). The SnO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub> delivered a low R<sub>s</sub> ( $7.00 \pm 1.1 \Omega \cdot \text{cm}^2$ ) value compared to the R<sub>s</sub> ( $14.72 \pm 2.09 \Omega \cdot \text{cm}^2$ ) of cells with SnO<sub>2</sub> only, leading to better charge extraction and passivation of trap states and/or pinholes at the perovskite and SnO<sub>2</sub> interface. Furthermore, R<sub>sh</sub> calculated for cells with SnO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub> layer ( $8.27 \pm 1.93 \text{ k}\Omega \cdot \text{cm}^2$ ) is much higher compared to cells with SnO<sub>2</sub> only ( $1.4 \pm 0.35 \text{ k}\Omega \cdot \text{cm}^2$ )

which is a result of better interface and/or perovskite film formation over the SnO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub> layer and lower recombination[39]. Note that Al<sub>2</sub>O<sub>3</sub> is a high band gap insulator[42].



**Fig. 3.** (a) J-V curves of SnO<sub>2</sub> and SnO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub> in dark. Arceo measurements carried out of perovskite solar cell device using ITO/SnO<sub>2</sub> and ITO/SnO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub> bilayers under white light irradiation (b) OCVD in light (OCVD in dark inset after switching off the irradiation), and (c) Series resistance (R<sub>s</sub>, open squares) and shunt resistance (R<sub>sh</sub>, closed circles) extracted from the J-V curves of the four cells each under 1 sun irradiation (d) Drop of CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> in DMF:DMSO on different ETLs: showing improvement in wettability after Al<sub>2</sub>O<sub>3</sub> layer deposition over SnO<sub>2</sub> ETL.

The higher surface roughness of the compact  $\text{SnO}_2/\text{Al}_2\text{O}_3$  bi-compact layer compared to the  $\text{SnO}_2$  layer only is likely to be the key reason behind these differences leading to improved interfacial growth of the perovskite and its interface area with the electron-extracting composite electrode [15]. We also observed that the presence of UV-irradiated  $\text{Al}_2\text{O}_3$  enhanced the wettability of  $\text{SnO}_2$  layer which determines a larger surface area and better wetting of the precursor (also due to higher surface roughness as discussed in figure 2 ) as well as network connection and interfacial growth of the perovskite for enhanced charge injection at the interface of perovskite and bottom ETL layer as shown in figure 3 (d) [43, 44].

We also measured the contact potential difference of the ITO/ETL surfaces via Kelvin probe measurements to see whether the application of the metal oxides gave rise to any significant changes in the work function (WF) of the electrodes. With reference to clean ITO electrodes for which  $\text{WF} = 4.70$  eV, the WF for ITO/ $\text{SnO}_2$  was  $4.84 \pm 0.12$  eV and that of ITO/ $\text{SnO}_2/\text{Al}_2\text{O}_3$  was  $4.72 \pm 0.05$  eV. Thus, the  $\text{Al}_2\text{O}_3$  overlayer also brings the work function of the electron-extracting electrode 0.1 eV closer to the conduction band of the perovskite solar cell, thereby contributing to the explanation of the higher forward currents at large voltages in the dark. It is very interesting to note that, whereas for the other type of composite bi-layer we had previously developed, i.e.  $\text{SnO}_2/\text{MgO}$ , the insulating  $\text{MgO}$  overlayer deposited from a precursor solution (rather than from a nanoparticle solution as in this  $\text{Al}_2\text{O}_3$  case) smoothed the surface and its main effect was to decrease the reverse current in the dark current plots [4] and thus limit back-recombination from the electrode, here the main improvement seen is in forward bias as a result of a lower work function, a more effective charge extraction and better film forming properties as well as maintaining a low reverse current. Thus, the application of thin insulating metal-oxide interlayers over the main transporting compact layers can have two main beneficial different effects apart from suppressing pinholes and trap states (valid for both cases) and/or varying the work function of the electrode which need to be distinguished: a) minimization of charge recombination by enabling electron tunneling from the perovskite to the electrode but suppressing back recombination, or by the small  $\text{Al}_2\text{O}_3$  nanoparticles more selectively covering those pinhole/defect areas in the underlying compact layer; b) improving perovskite growth and quality of the semiconductor/ETL interface. These effects can even come into play differently when considering the same thin interlayer material, i.e.  $\text{Al}_2\text{O}_3$ , but deposited with different techniques. For example, atomic layer deposition ensures a very thin conformal layer (case a) compared to the rougher surface via solution processed nano-particle thin films here shown (case b) [4, 45-48] and better extracting properties. The enhanced interface area between perovskite and transport layers and improved interfacial growth of the

perovskite, as well as reducing the defects/pinholes at the electrode, are likely the major reason for the reduction of charge recombination and improved electron extraction of the perovskite solar cells [15].

#### IV. CONCLUSION

We have fabricated planar PSCs using  $\text{SnO}_2/\text{Al}_2\text{O}_3$  double ETL between perovskite and ITO bottom electrode. The performance of PSCs was improved significantly after incorporation of  $\text{SnO}_2/\text{Al}_2\text{O}_3$  double ETL. Importantly,  $\text{SnO}_2/\text{Al}_2\text{O}_3$  double ETLs enhanced the PCE of PSCs when measured under 1 sun illumination compared to cells with  $\text{SnO}_2$  only. The PSCs with  $\text{SnO}_2/\text{Al}_2\text{O}_3$  double ETL delivered a maximum PCE of 20.1% and a steady state efficiency of 17.8% under 1 sun illumination. These values were 20-30% higher in relative terms compared to that of cells with  $\text{SnO}_2$  only (15.3% and 14.9% respectively). We observed that the wettability of  $\text{SnO}_2$  layer was effectively enhanced with incorporation of UV-irradiated  $\text{Al}_2\text{O}_3$  layer. Perovskite solar cells with double ETL delivered higher rectification ratios compared to cells with  $\text{SnO}_2$  only. All layers of our device were solution-processed at low temperature ( $\leq 150$  °C). This is a very simple and effective approach for fabricating highly-efficient perovskite cells.

#### APPENDIX

Appendices, if needed, appear before the acknowledgement.

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